To our customers,

Old Company Name in Catalogs and Other Documents

On April 1st, 2010, NEC Electronics Corporation merged with Renesas Technology Corporation, and Renesas Electronics Corporation took over all the business of both companies. Therefore, although the old company name remains in this document, it is a valid Renesas Electronics document. We appreciate your understanding.

Renesas Electronics website: http://www.renesas.com

April 1st, 2010
Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

Send any inquiries to http://www.renesas.com/inquiry.

RENESAS

MOS FIELD EFFECT TRANSISTOR
2SK3811

SWITCHING
N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3811 is N-channel MOS Field Effect Transistor designed for high current switching applications.

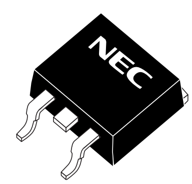
ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3811-ZP	TO-263 (MP-25ZP)

FEATURES

- Super low on-state resistance
  $R_{DS(on)}$ = 1.8 mΩ MAX. (V_{GS} = 10 V, I_D = 55 A)
- High Current Rating: $I_{D(DC)}$ = ±110 A

(TO-263)



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V_{GS} = 0 V)	V_{DSS}	40	V
Gate to Source Voltage (V_{DS} = 0 V)	V_{GSS}	±20	V
Drain Current (DC) (T_C = 25°C)	$I_{D(DC)}$	±110	A
Drain Current (pulse) Note1	$I_{D(pulse)}$	±440	A
Total Power Dissipation (T_C = 25°C)	P_{T1}	213	W
Total Power Dissipation (T_A = 25°C)	P_{T2}	1.5	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T_{stg}	–55 to +150	°C
Single Avalanche Energy Note2	E_{AS}	518	mJ
Repetitive Avalanche Current Note3	I_{AR}	72	A
Repetitive Avalanche Energy Note3	E_{AR}	518	mJ

Notes 1. PW ≤ 10 μs, Duty Cycle ≤ 1%

2. Starting T_{ch} = 25°C, V_{DD} = 20 V, R_G = 25 Ω, V_{GS} = 20 → 0 V, L = 100 μH

3. R_G = 25 Ω, $T_{ch(peak)}$ ≤ 150°C

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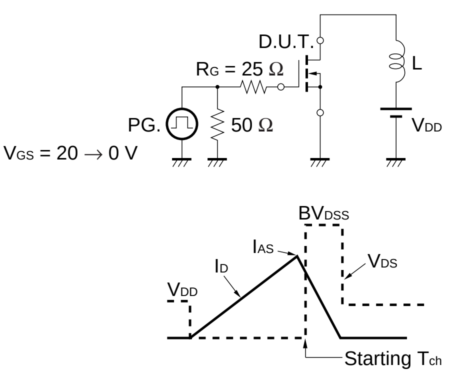
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

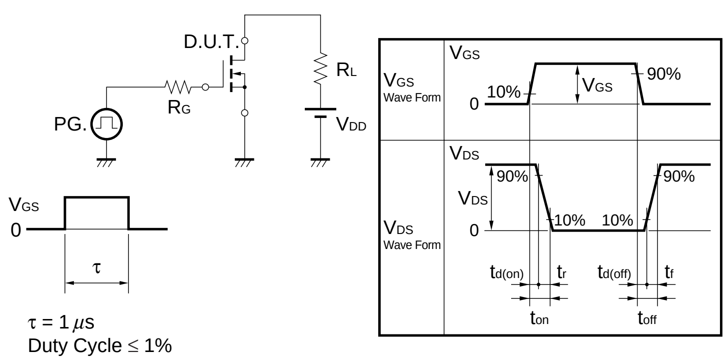
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 40 V, V_{GS} = 0 V			10	μA
Gate Leakage Current	I_{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA
Gate Cut-off Voltage	$V_{GS(off)}$	V_{DS} = 10 V, I_D = 1 mA	2.0	3.0	4.0	V
Forward Transfer Admittance Note	| y_{fs} |	V_{DS} = 10 V, I_D = 55 A	45	89		S
Drain to Source On-state Resistance Note	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 55 A		1.4	1.8	mΩ
Input Capacitance	C_{iss}	V_{DS} = 10 V		17700		pF
Output Capacitance	C_{oss}	V_{GS} = 0 V		2200		pF
Reverse Transfer Capacitance	C_{rss}	f = 1 MHz		1300		pF
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 20 V, I_D = 55 A		54		ns
Rise Time	t_r	V_{GS} = 10 V		140		ns
Turn-off Delay Time	$t_{d(off)}$	R_G = 0 Ω		130		ns
Fall Time	t_f			21		ns
Total Gate Charge	Q_G	V_{DD} = 32 V		260		nC
Gate to Source Charge	Q_{GS}	V_{GS} = 10 V		57		nC
Gate to Drain Charge	Q_{GD}	I_D = 110 A		83		nC
Body Diode Forward Voltage Note	$V_{F(S-D)}$	I_F = 110 A, V_{GS} = 0 V		0.87	1.5	V
Reverse Recovery Time	t_{rr}	I_F = 110 A, V_{GS} = 0 V		60		ns
Reverse Recovery Charge	Q_{rr}	di/dt = 100 A/μs		80		nC

Note Pulsed

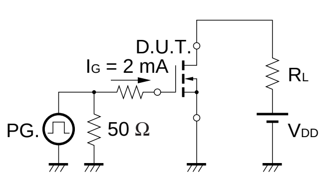
TEST CIRCUIT 1 AVALANCHE CAPABILITY



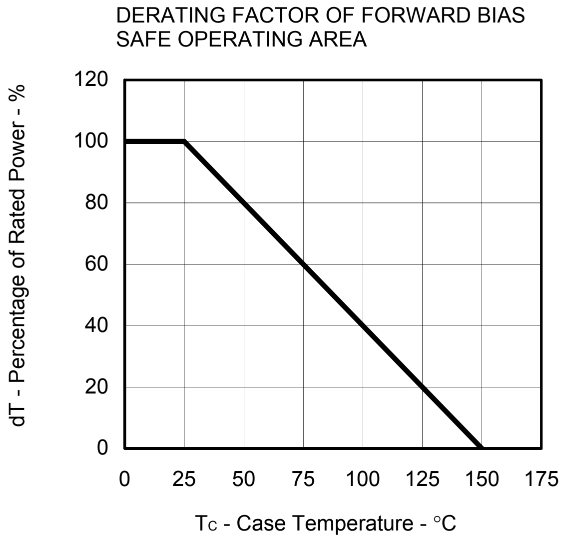
TEST CIRCUIT 2 SWITCHING TIME

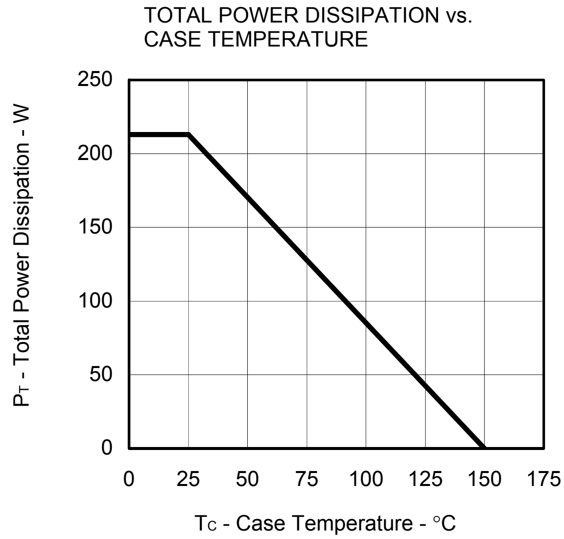


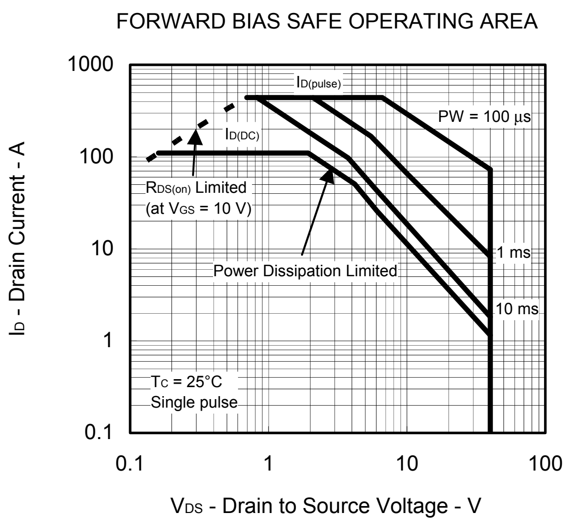
TEST CIRCUIT 3 GATE CHARGE

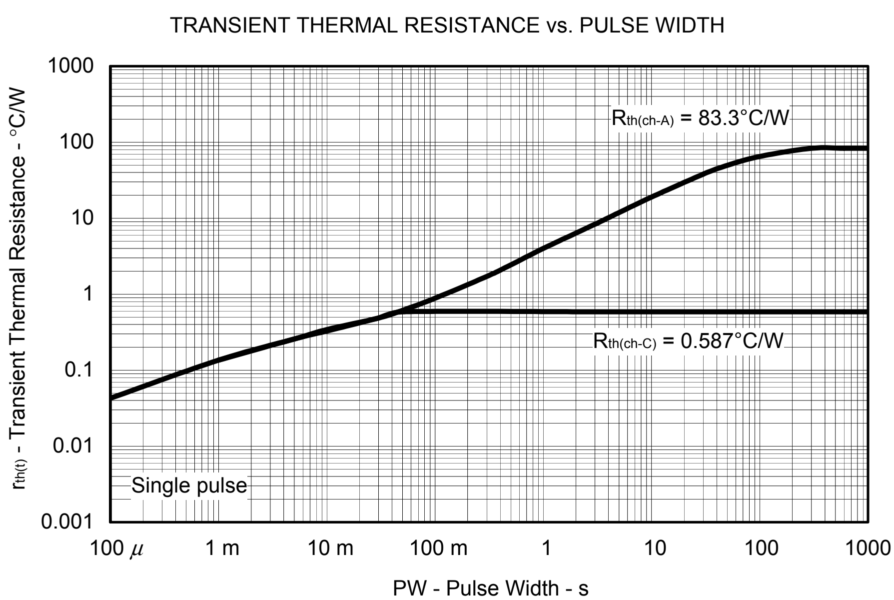


TYPICAL CHARACTERISTICS (T_A = 25°C)

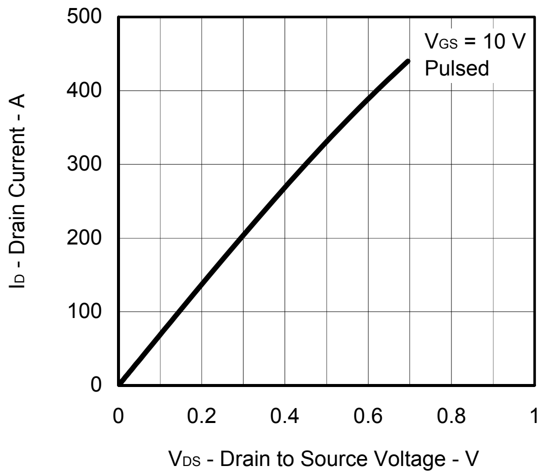




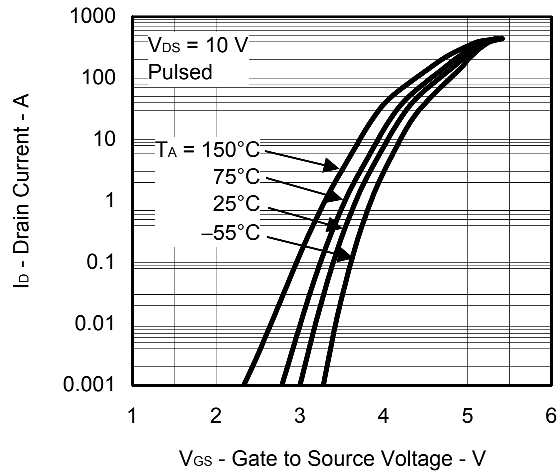




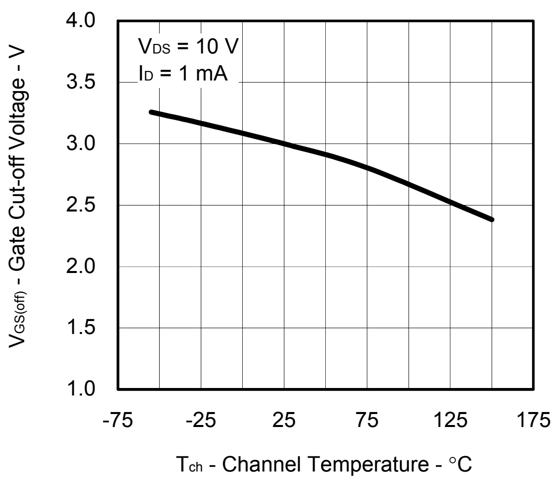
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



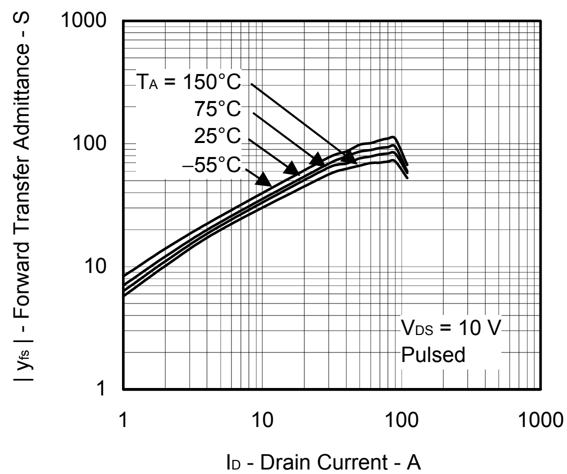
FORWARD TRANSFER CHARACTERISTICS



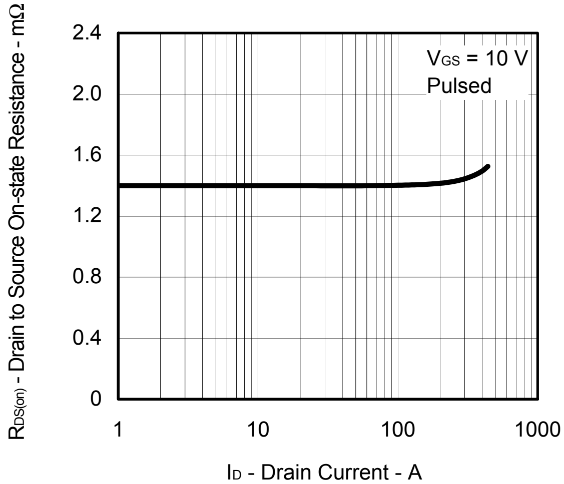
GATE CUT-OFF VOLTAGE vs.
CHANNEL TEMPERATURE



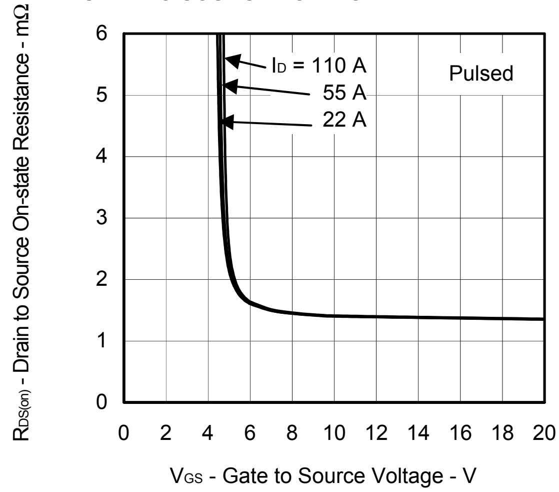
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



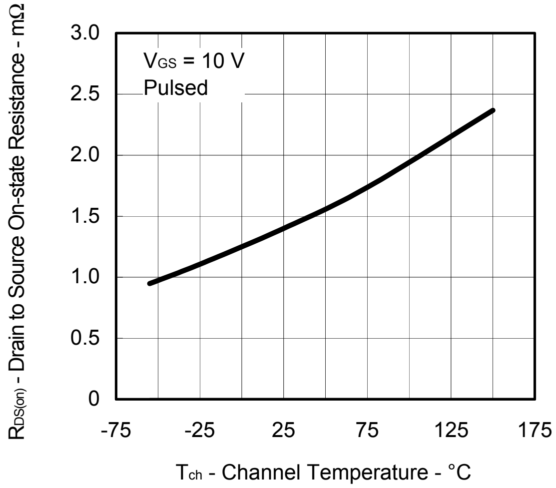
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENT



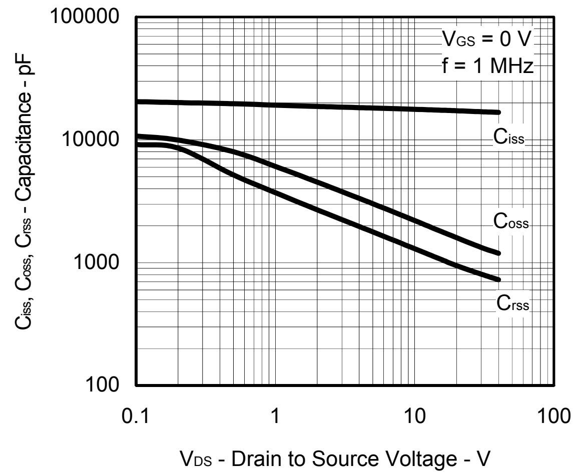
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



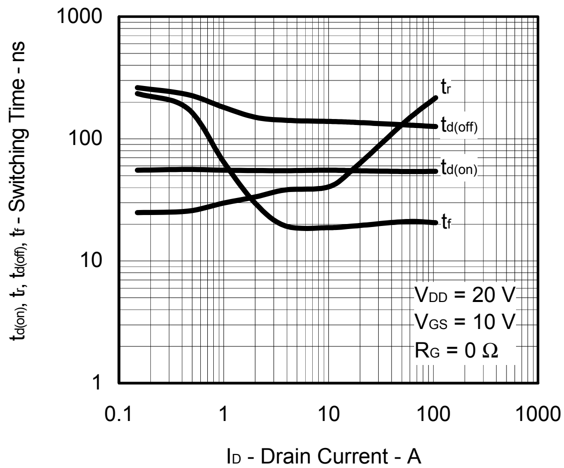
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



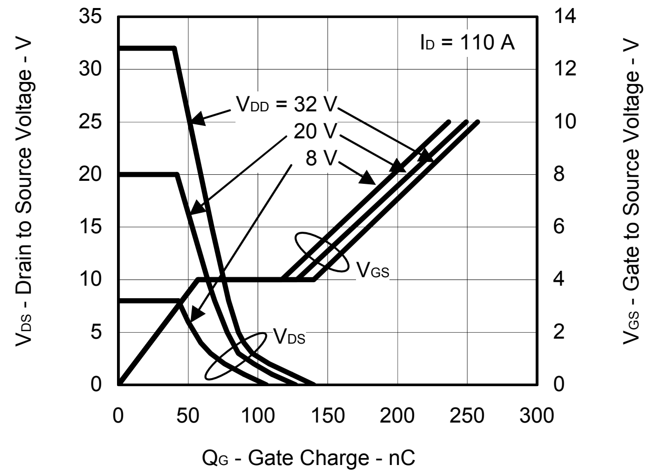
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



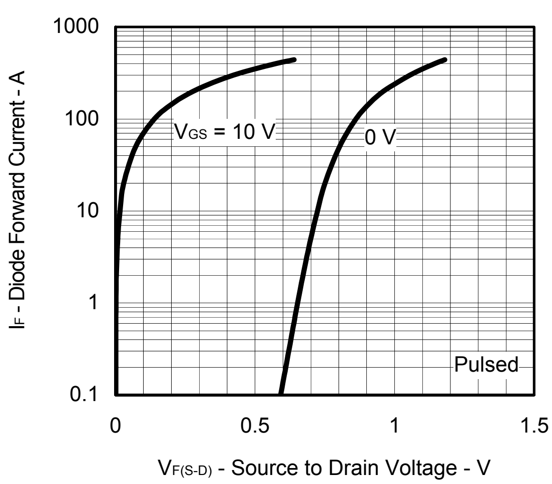
SWITCHING CHARACTERISTICS



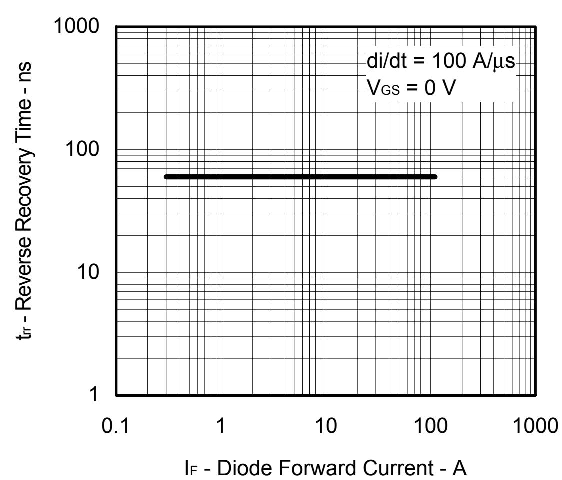
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



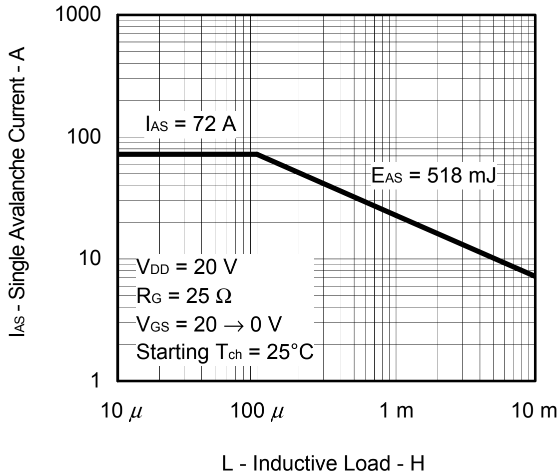
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



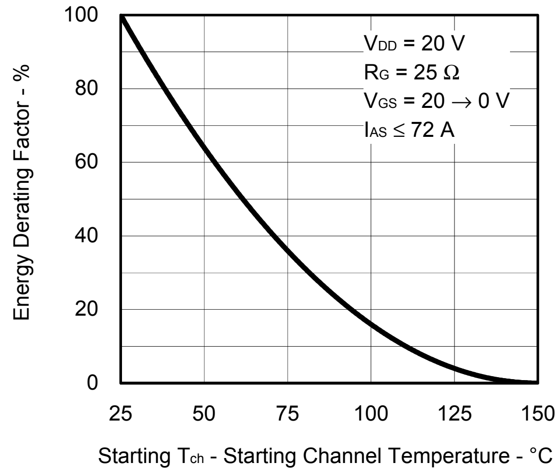
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD

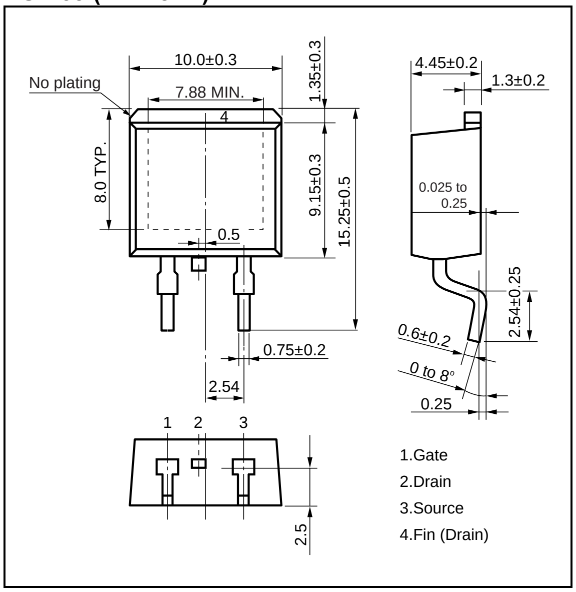


SINGLE AVALANCHE ENERGY DERATING FACTOR

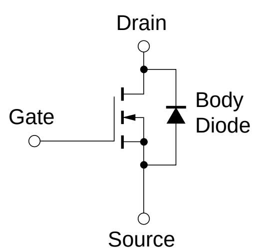


PACKAGE DRAWING (Unit: mm)

TO-263 (MP-25ZP)



EQUIVALENT CIRCUIT



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001
Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

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Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:
moschip.ru
moschip.ru_4
moschip.ru_6
moschip.ru_9